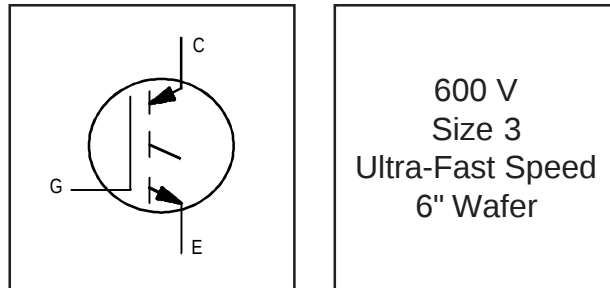


IRG4CC30UB

IRG4CC30UB IGBT Die in Wafer Form



Electrical Characteristics (Wafer Form)

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	4.5V Max.	$I_C = 10A$, $T_J = 25^\circ C$, $V_{GE} = 15V$
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600V Min.	$T_J = 25^\circ C$, $I_{CES} = 250\mu A$, $V_{GE} = 0V$
$V_{GE(th)}$	Gate Threshold Voltage	3.0V Min., 6.0V Max.	$V_{GE} = V_{CE}$, $T_J = 25^\circ C$, $I_C = 250\mu A$
I_{CES}	Zero Gate Voltage Collector Current	300 μA Max.	$T_J = 25^\circ C$, $V_{CE} = 600V$
I_{GES}	Gate-to-Emitter Leakage Current	$\pm 11\mu A$ Max.	$T_J = 25^\circ C$, $V_{GE} = \pm 20V$

Mechanical Data

Normal Backmetal Composition, Thickness:	Cr-Ni / V-Ag (1 kA-2kA-2.5kA)
Normal Front Metal Composition, Thickness:	99% Al, 1% Si (3 microns)
Dimensions:	0.141" x 0.164"
Wafer Diameter:	150mm, with std. < 100 > flat
Wafer thickness:	.015" + / -.003"
Relevant Die Mechanical Dwg. Number	01-5225
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Ink Dot Location	Consistent throughout same wafer lot
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : IRG4BC30U

Die Outline

